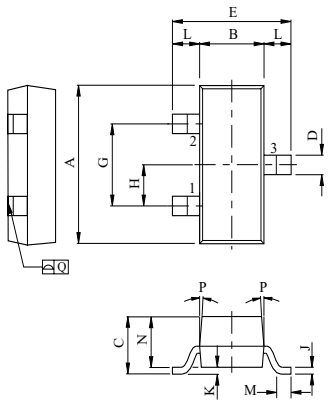
KN4402S/4403S

EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

FEATURES

· Complementary to the KN4400S/4401S



DIM	MILLIMETERS
A	2.93±0.20
B	1.30+0.20/-0.15
C	1.30 MAX
D	0.40+0.15/-0.05
E	2.40+0.30/-0.20
G	1.90
H	0.95
J	0.13+0.10/-0.05
K	0.00 ~ 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/-0.10
P	7°
Q	0.1 MAX

1. EMITTER
2. BASE
3. COLLECTOR

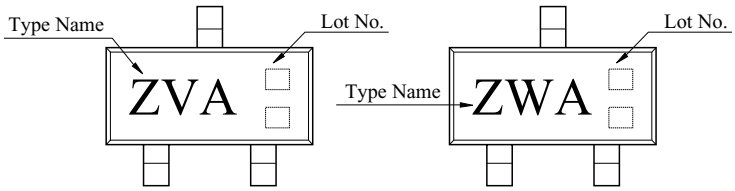
SOT-23

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-600	mA
Collector Power Dissipation	P_C *	350	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 150	℃

Note : * Package Mounted On 99.5% Alumina 10×8×0.6㎜)

Marking



MARK SPEC

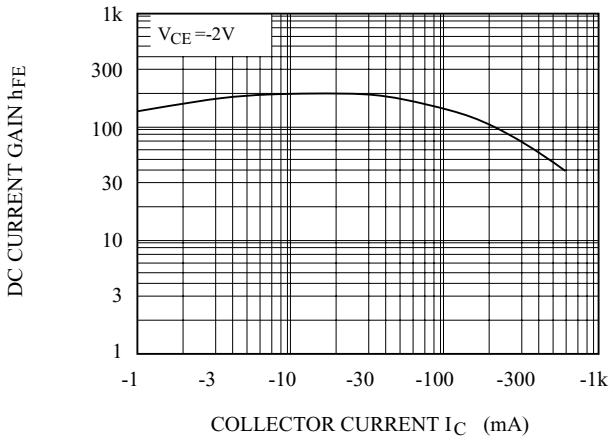
TYPE	MARK
KN4402S	ZVA
KN4403S	ZWA

ELECTRICAL CHARACTERISTICS (Ta=25°C)

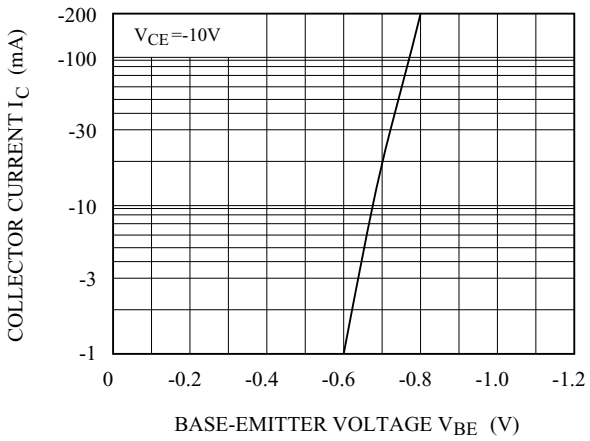
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CEX}	V_{CE}=-35V, V_{EB}=-0.4V	-	-	-100	nA
Collector Cut-off Current		I_{CBO}	V_{CB}=-40V, I_E=0	-	-	-100	nA
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	I_C=-100 μA, I_E=0	-40	-	-	V
Collector-Emitter Breakdown Voltage *		$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-40	-	-	V
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	I_E=-100 μA, I_C=0	-5	-	-	V
DC Current Gain *	KN4403S	h_{FE}(1)	V_{CE}=-1V, I_C=-0.1mA	30	-	-	
	KN4402S	h_{FE}(1)	V_{CE}=-1V, I_C=-1mA	30	-	-	
	KN4403S	h_{FE}(2)		60	-	-	
	KN4402S	h_{FE}(2)	V_{CE}=-1V, I_C=-10mA	50	-	-	
	KN4403S	h_{FE}(3)		100	-	-	
	KN4402S	h_{FE}(3)	V_{CE}=-2V, I_C=-150mA	50	-	150	
	KN4403S	h_{FE}(4)		100	-	300	
	KN4402S	h_{FE}(4)	V_{CE}=-2V, I_C=-500mA	20	-	-	
	KN4403S	h_{FE}(5)		20	-	-	
Collector-Emitter Saturation Voltage *		$V_{CE(sat)}$1	I_C=-150mA, I_B=-15mA	-	-	-0.4	V
		$V_{CE(sat)}$2	I_C=-500mA, I_B=-50mA	-	-	-0.75	
Base-Emitter Saturation Voltage *		$V_{BE(sat)}$1	I_C=-150mA, I_B=-15mA	-0.75	-	-0.95	V
		$V_{BE(sat)}$2	I_C=-500mA, I_B=-50mA	-	-	-1.3	
Transition Frequency		f_T	V_{CE}=-10V, I_C=-20mA f=100MHz	200	-	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	-	8.5	pF

* Pulse Test : Pulse Width≦300 μS, Duty Cycle≦2%.

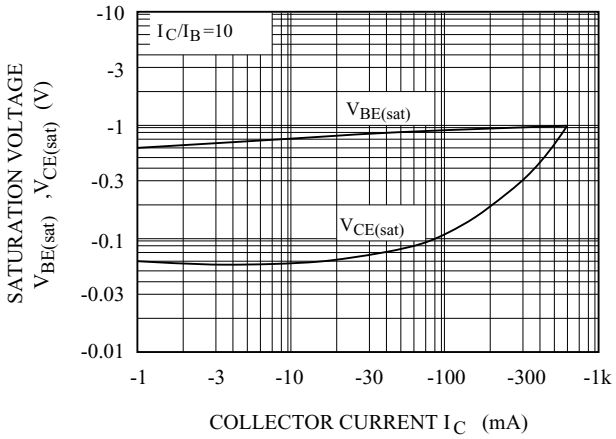
h_{FE} - I_C



I_C - V_{BE}



$V_{BE(sat)}$,$V_{CE(sat)}$ - I_C



C_{cb} - V_{CB}

